

PART NUMBERING SYSTEM

ISOMOS™ PHOTO MOS RELAY

STANDARD & SOP

Example part number:

WPPM - 35 2 8 S - TRU
(1) (2) (3) (4) (5) (6)

(1) Photo MOS

(2) Load Voltage

06: 60V
10: 100V
20: 200V
35: 350V
40: 400V

(3) Contact Characteristics

2: 1 Form A
4: 1 Form B
6: 1 Form A + 1 Form B
8: Dual Form A
10: Dual Form B

(4) Pin Configuration

4: 4 pin
6: 6 pin
8: 8 pin
16: 16 pin

(5) Package Types

D: DIP
A: SMD
S: SOP

(6) Taping

TLD: Tape Direction Left
TRU: Tape Direction Right

CUSTOM VERSIONS

Example part number:

WPPML - 35 2 4 S - TRU
(1) (2) (3) (4) (5) (6)

(1) Photo MOS Custom

(2) Load Voltage

35: 350V
06: 60V (only available in SOP package)

(3) Contact Characteristics

2: 1 Form A

(4) Pin Configuration

4: 4 pin

(5) Package Types

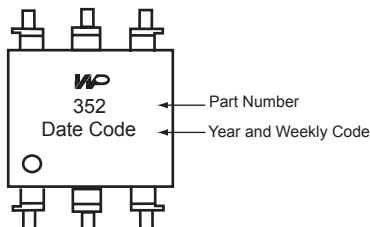
D: DIP
A: SMD
S: SOP

(6) Taping

TLD: Tape Direction Left
TRU: Tape Direction Right

Not all combinations are available

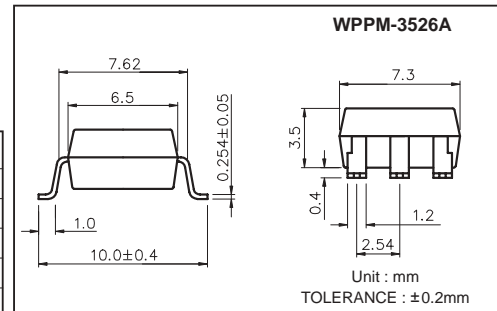
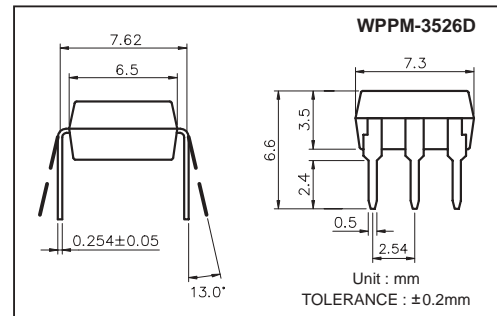
PART MARKING SYSTEM



Features

1. Normally open, single pole single throw.
2. Control 350VAC or DC voltage.
3. Switch 130mA loads.
4. LED control current, 5mA.
5. Low ON-resistance.
6. dv/dt, >500V/mS.
7. Isolation test voltage, 3750VRMS.

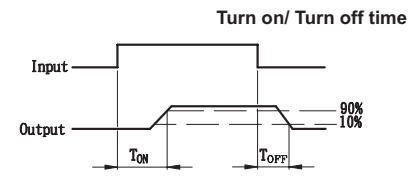
Part Numbering System & Part Marking System: Page 1.



Absolute Maximum Ratings

(Ta=25°C)

Emitter (Input)	Detector (Output)
Reverse Voltage.....5.0V	Output Breakdown Voltage±350V
Continuous Forward Current50mA	Continuous Load Current±130mA
Peak Forward Current1A	Power Dissipation500mW
Power Dissipation100mW	
Derate Linearly from 25°C1.3mW/°C	
General Characteristics	
Isolation Test Voltage3750VRMS	Storage Temperature Range-40°C to +125°C
Isolation Resistance	Operating Temperature Range...-30°C to +85°C
V _{IO} = 500V, T _A = 25°C ≥10 ¹⁰ Ω	Junction Temperature..... 100°C
Total Power Dissipation550mW	Soldering Temperature,
Derate Linearly from 25°C2.5mW/°C	2mm from case, 10 sec260°C



Electro-optical Characteristics

(Ta=25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Emitter (Input)							
Forward Voltage	V _F	I _F = 10mA		1.2	1.5	V	
Operation Input Current	I _{FORN}	V _L = ±20V, I _L = 100mA, t = 10mS			5	mA	
Recovery Input Current	I _{FOFF}	V _L = ±20V, I _L ≤ 5uA	0.2			mA	
Detector (Output)							
Output Breakdown Voltage	V _B	I _B = 50uA	350			V	
Output Off-State Leakage	I _{TOFF}	V _T = 100V, I _F = 0mA		0.2	1	uA	
I/O Capacitance	C _{ISO}	I _F = 0, f = 1MHz		6		pF	
ON Resistance	Connection	A	I _L = 100mA, I _F = 10mA		20	30	Ω
		B			10	15	
		C			5	7.5	
Turn-On Time	T _{ON}	I _F = 10mA, V _L = ±20V		0.3	1.0	mS	
Turn-Off Time	T _{OFF}	t = 10mS, I _L = ±100mA		0.7	1.5	mS	

MOS Relay Schematic and Wiring Diagrams

Type	Schematic	Output configuration	Load	Connection	Wiring Diagrams
3526D & 3526A		1a	AC/DC	A	
			DC	B	
			DC	C	

Data Curve

